

2SC1624 2SC1625

SILICON NPN PLANAR TYPE

MEDIUM POWER AMPLIFIER APPLICATIONS.
DRIVER STAGE AMPLIFIER APPLICATIONS.

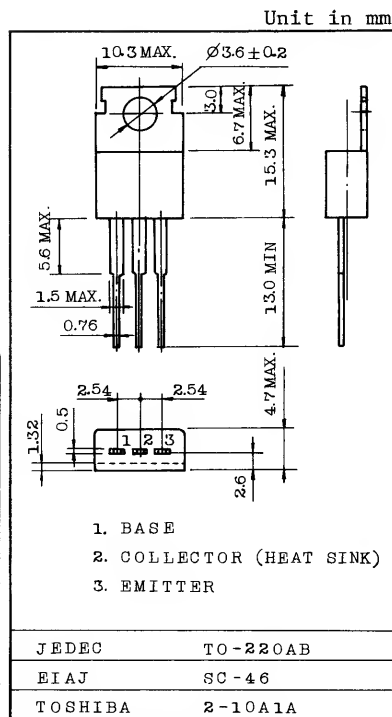
FEATURES:

High Breakdown Voltage : $V_{CE0}=120V$ (2SC1624)

Complementary to 2SA814 and 2SA815.

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage	2SC1624	V_{CB0}	120	V
	2SC1625		100	
Collector-Emitter Voltage	2SC1624	V_{CE0}	120	V
	2SC1625		100	
Emitter-Base Voltage		V_{EB0}	5	V
Collector Current		I_C	1	A
Emitter Current		I_E	-1	A
Collector Power Dissipation (Tc=25°C)		P_C	15	W
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	-55~150	°C



Mounting Kit No. AC75
Weight : 1.9g

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB}=50V, I_E=0$	-	-	1.0	μA
Emitter Cut-off Current		I_{EBO}	$V_{EB}=5V, I_C=0$	-	-	1.0	μA
Collector-Emitter Breakdown Voltage	2SC1624	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	120	-	-	V
	2SC1625			100	-	-	
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	$I_E=1mA, I_C=0$	5	-	-	V
DC Current Gain	$h_{FE(1)}$ (Note)		$V_{CE}=5V, I_C=150mA$	70	-	240	
	$h_{FE(2)}$		$V_{CE}=5V, I_C=500mA$	40	-	-	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$	-	-	0.5	V
Base-Emitter Voltage		V_{BE}	$V_{CE}=5V, I_C=500mA$	-	-	1.0	V
Transition Frequency		f_T	$V_{CE}=5V, I_C=150mA$	10	30	-	MHz
Collector Output Capacitance		C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$	-	20	-	pF

Note : $h_{FE(1)}$ Classification 0 : 70~140, Y : 120~240

